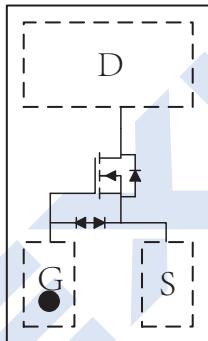
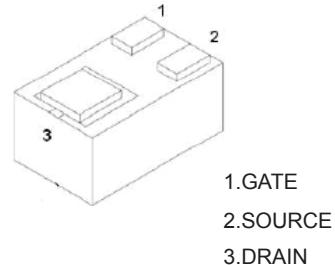


**N-Channel MOSFET****2KK6013DFN****■ Features**

- $V_{DS}$  (V) = 50 V
- $I_D$  = 0.3 A
- $R_{DS(ON)}$  (at  $V_{GS}$  = 10 V) = 1.2 Ω
- $R_{DS(ON)}$  (at  $V_{GS}$  = 4.5 V) = 1.4 Ω
- $R_{DS(ON)}$  (at  $V_{GS}$  = 1.8 V) = 4.0 Ω
- ESD Protected

**DFN1006-3****■ Absolute Maximum Ratings ( $T_a$  = 25°C unless otherwise noted)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current (Note 1)	$I_D$	0.3	A
Pulsed Drain Current ( $t_p=10\mu s$ )	$I_{DM}$	0.9	
Power Dissipation (Note 1)	$P_D$	0.25	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	500	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	

Note 1. Surface mounted on FR4 board using the minimum recommended pad size.

## 2KK6013DFN

■ Electrical Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$\text{I}_d = 250 \mu\text{A}, \text{V}_{\text{GS}} = 0\text{V}$	50			V
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}} = 30 \text{ V}, \text{V}_{\text{GS}} = 0 \text{ V}$		1		$\mu\text{A}$
Gate to Source Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{DS}} = 0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$			$\pm 5$	
Gate to Source Threshold Voltage (Note 2)	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{I}_d = 250 \mu\text{A}$	0.8		1.5	V
Static Drain-Source On-Resistance (Note 2)	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}} = 10 \text{ V}, \text{I}_d = 0.45 \text{ A}$		1.2	1.8	$\Omega$
		$\text{V}_{\text{GS}} = 4.5 \text{ V}, \text{I}_d = 0.25 \text{ A}$		1.4	2	
		$\text{V}_{\text{GS}} = 2.5 \text{ V}, \text{I}_d = 0.01 \text{ A}$		2	6	
		$\text{V}_{\text{GS}} = 1.8 \text{ V}, \text{I}_d = 0.01 \text{ A}$		4		
Forward Transconductance (Note 2)	$\text{g}_{\text{FS}}$	$\text{V}_{\text{DS}} = 15 \text{ V}, \text{I}_d = 0.1 \text{ A}$		0.5		S
Diode Forward Voltage	$\text{V}_{\text{SD}}$	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{I}_s = 0.25 \text{ A}$			1.2	V
<b>DYNAMIC PARAMETERS (Note 4)</b>						
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, \text{V}_{\text{DS}} = 15 \text{ V}$		23		pF
Output Capacitance	$\text{C}_{\text{oss}}$			12		
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$			5		
Total Gate Charge	$\text{Q}_{\text{g(tot)}}$	$\text{V}_{\text{GS}} = 10 \text{ V}, \text{V}_{\text{DS}} = 30 \text{ V}, \text{I}_d = 0.1 \text{ A}$		1.6		nC
Threshold Gate Charge	$\text{Q}_{\text{g(th)}}$			0.25		
Gate Source Charge	$\text{Q}_{\text{gs}}$			0.4		
Gate Drain Charge	$\text{Q}_{\text{gd}}$			0.45		
<b>SWITCHING PARAMETERS (Note 4)</b>						
Turn-On Delay Time (Note 3)	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{GS}} = 5 \text{ V}, \text{V}_{\text{DD}} = 5 \text{ V}, \text{I}_d = 10 \text{ mA}, \text{R}_L = 500 \Omega, \text{R}_G = 10 \Omega$		8.6		ns
Turn-On Rise Time (Note 3)	$\text{t}_r$			4		
Turn-Off Delay Time (Note 3)	$\text{t}_{\text{d(off)}}$			23.8		
Turn-Off Fall Time (Note 3)	$\text{t}_f$			14.2		

Notes:

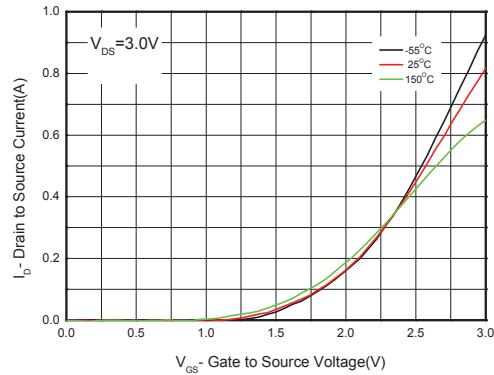
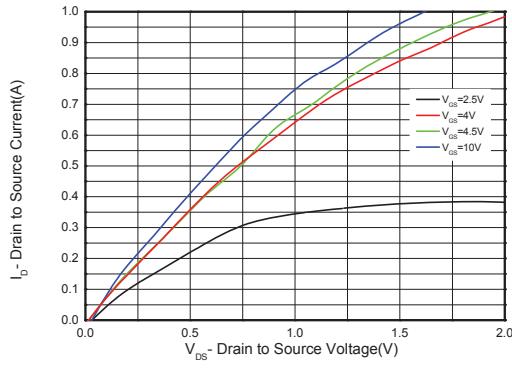
2. Pulse Test : Pulse width=300  $\mu\text{s}$ , duty cycle  $\leq 2\%$ .
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

## ■ Marking

Marking	B
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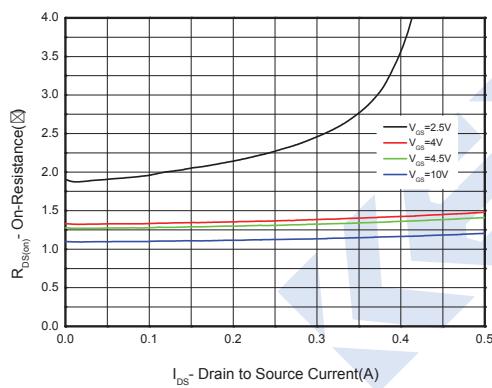
**2KK6013DFN**

## ■ Typical Characteristics

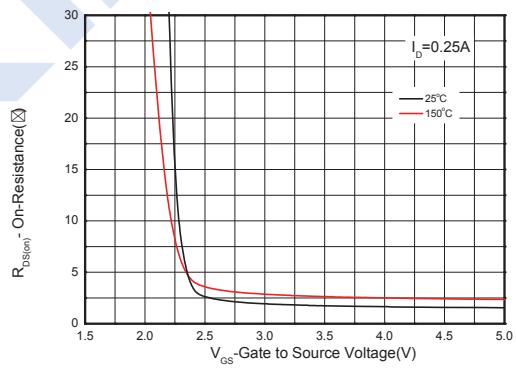


Output characteristics

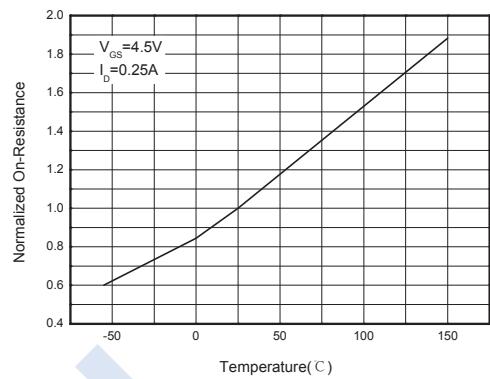
Transfer characteristics



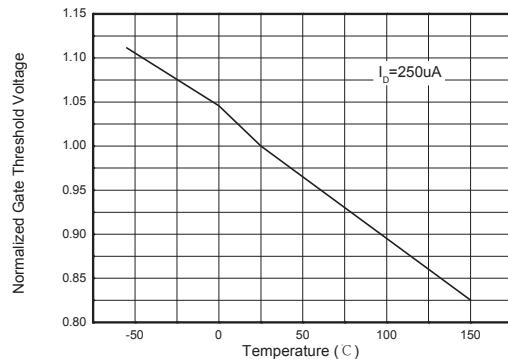
On-Resistance vs. Drain current



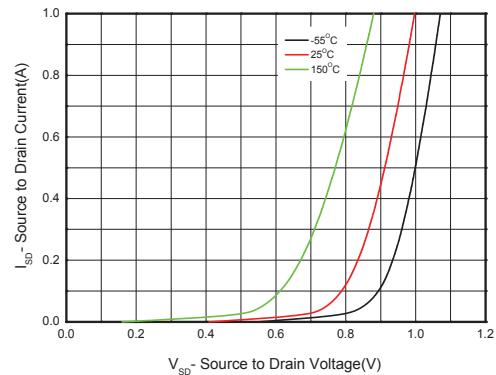
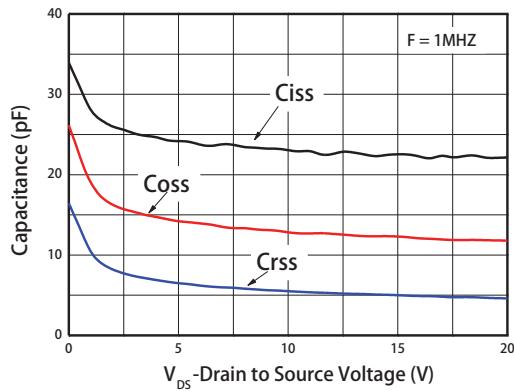
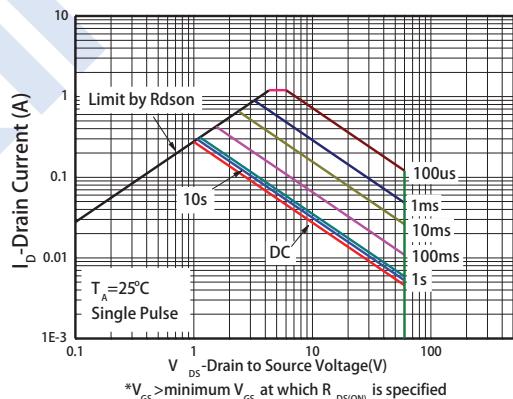
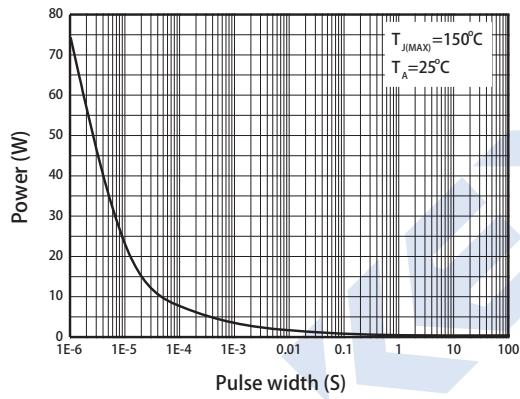
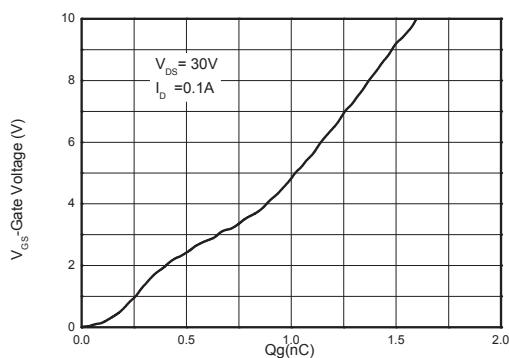
On-Resistance vs. Gate-to-Source voltage



On-Resistance vs. Junction temperature



Threshold voltage vs. Temperature

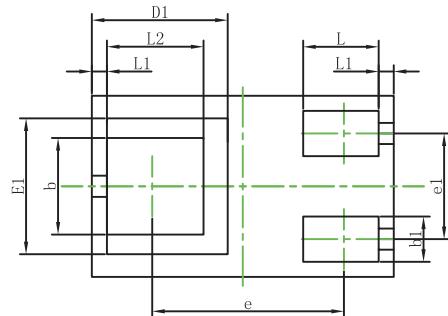
**2KK6013DFN****Capacitance****Body diode forward voltage****Single pulse power****Safe operating power****Gate charge Characteristics**

## 2KK6013DFN

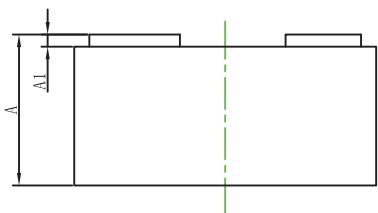
## ■ DFN1006-3 Package Outline Dimensions



TOP VIEW



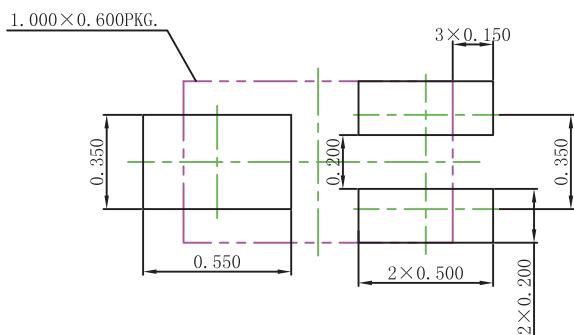
BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.100	0.000	0.004
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.450REF.		0.018REF.	
E1	0.450REF.		0.018REF.	
b	0.270	0.370	0.011	0.015
b1	0.100	0.200	0.004	0.008
e	0.635REF.		0.025REF.	
e1	0.300	0.400	0.012	0.016
L	0.200	0.300	0.008	0.012
L1	0.050REF.		0.002REF.	
L2	0.270	0.370	0.011	0.015

## ■ DFN1006-3 Suggested Pad Layout



## Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.050\text{mm}$ .
3. The pad layout is for reference purposes only.